IR-Lumineszenzdiode (940nm) mit hoher Ausgangsleistung in SMR® Gehäuse
High Power Infrared Emitter (940nm) in SMR® Package

Lead (Pb) Free Product - RoHS CompliantLead (Pb) Free Product - RoHS

SFH 4542
SFH 4543

SFH 4542

SFH 4543

gemäß OS-PCN-2009-021-A2

acc. to OS-PCN-2009-021-A2

Wesentliche Merkmale

- Infrarot LED mit hoher Ausgangsleistung
- SMR® (Surface Mount Radial) Gehäuse
- Gehäusegleich mit Fotodiode SFH 2500
- Kurze Schaltzeiten

Features

- High Power Infrared LED
- SMR® (Surface Mount Radial) package
- Same package as photodiode SFH 2500
- Short switching times

Anwendungen

- Sensorik
- Diskrete Lichtschranken
- Diskrete Optokoppler

Applications

- Sensor technology
- Discrete interrupters
- Discrete optocouplers

Sicherheitshinweise

Je nach Betriebsart emittieren diese Bauteile hochkonzentrierte, nicht sichtbare Infrarot-Strahlung, die gefährlich für das menschliche Auge sein kann. Produkte, die diese Bauteile enthalten, müssen gemäß den Sicherheits-richtlinien der IEC-Normen 60825-1 und 62471 behandelt werden.

Safety Advices

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 and IEC 62471.

Typ **Type**	**Bestellnummer** **Ordering Code**	**Strahlstärkegruppierung**[1] (I_F = 100 mA, t_p = 20 ms) **Radiant Intensity Grouping**[1] I_e (mW/sr)
SFH 4542	Q65110A8093	≥ 100 (typ. 230)
SFH 4543	Q65110A8094	≥ 100 (typ. 230)

[1] gemessen bei einem Raumwinkel Ω = 0.01 sr / measured at a solid angle of Ω = 0.01 sr

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Grenzwerte (T_A = 25 °C)
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	T_{op} , T_{stg}	– 40 … + 85	°C
Sperrspannung Reverse voltage	V_R	5	V
Vorwärtsgleichstrom Forward current	I_F	100	mA
Stoßstrom, t_p = 100 µs, D = 0 Surge current	I_{FSM}	1	A
Verlustleistung Power dissipation	P_{tot}	180	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je 20 mm^2 Thermal resistance junction - ambient mounted on PC-board (FR4), padsize 20 mm^2 each	R_{thJA}	300	K/W

Kennwerte (T_A = 25 °C)
Characteristics

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission I_F = 100 mA	λ_{peak}	950	nm
Schwerpunkt-Wellenlänge der Strahlung Centroid wavelength I_F = 100 mA	$\lambda_{centroid}$	940	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} I_F = 100 mA	$\Delta\lambda$	42	nm
Abstrahlwinkel Half angle	φ	± 10	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm^2
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	0.3 × 0.3	mm²

Kennwerte (T_A = 25 °C)
Characteristics (cont'd)

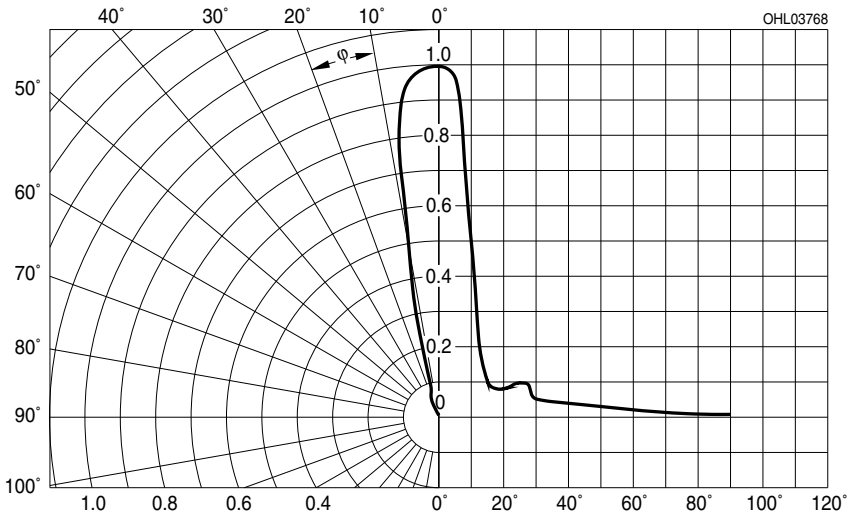
Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**	**Einheit** **Unit**
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei I_F = 100 mA, R_L = 50 Ω Switching times, I_e from 10% to 90% and from 90% to 10%, I_F = 100 mA, R_L = 50 Ω	t_r, t_f	12	ns
Durchlassspannung Forward voltage I_F = 100 mA, t_p = 20 ms I_F = 1 A, t_p = 100 µs	 V_F V_F	 1.5 (< 1.8) 2.4 (< 3.0)	 V V
Sperrstrom Reverse current	I_R	not designed for reverse operation	µA
Gesamtstrahlungsfluss Total radiant flux I_F = 100 mA, t_p = 20 ms	$\Phi_{e\ typ}$	65	mW
Temperaturkoeffizient von I_e bzw. Φ_e, I_F = 100 mA Temperature coefficient of I_e or Φ_e, I_F = 100 mA	TC_I	– 0.5	%/K
Temperaturkoeffizient von V_F, I_F = 100 mA Temperature coefficient of V_F, I_F = 100 mA	TC_V	– 3	mV/K
Temperaturkoeffizient von λ, I_F = 100 mA Temperature coefficient of λ, I_F = 100 mA	TC_λ	+ 0.3	nm/K

Strahlstärke I_e in Achsrichtung[1)]
gemessen bei einem Raumwinkel Ω = 0.01 sr
Radiant Intensity I_e in Axial Direction
at a solid angle of Ω = 0.01 sr

Bezeichnung Parameter	Symbol	Werte Values			Einheit Unit
		-AW	-BW	-CW	
Strahlstärke Radiant intensity I_F = 100 mA, t_p = 20 ms	$I_{e\ min}$ $I_{e\ max}$	100 200	160 320	250 500	mW/sr mW/sr
Strahlstärke Radiant intensity I_F = 1 A, t_p = 25 µs	$I_{e\ typ}$	1000	1700	2600	mW/sr

[1)] Nur eine Gruppe in einer Verpackungseinheit (Streuung kleiner 2:1) /
Only one bin in one packing unit (variation lower 2:1)

Abstrahlcharakteristik
Radiation Characteristics $I_{rel} = f(\varphi)$



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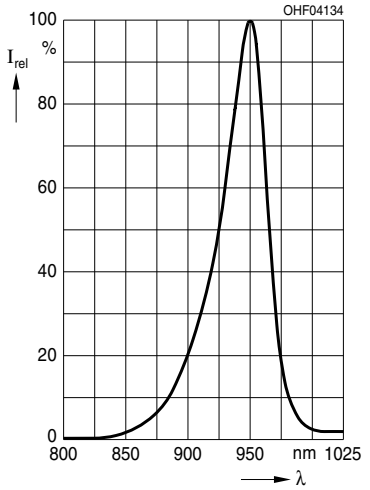
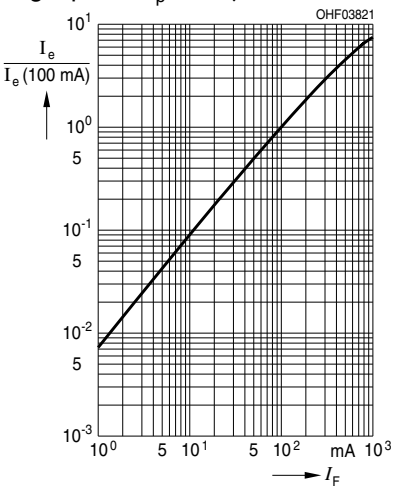
Relative Spectral Emission
$I_{rel} = f(\lambda)$

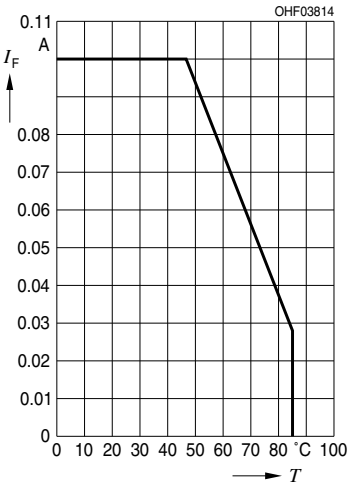


Radiant Intensity $\frac{I_e}{I_e\ 100\ mA} = f(I_F)$

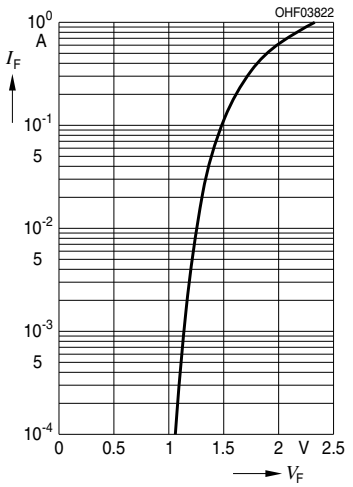
Single pulse, t_p = 25 µs



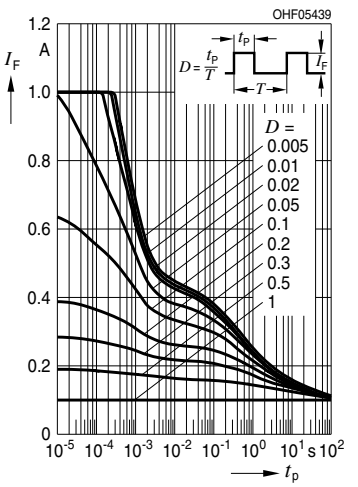
Max. Permissible Forward Current
$I_F = f(T_A)$, R_{thJA} = 300 K/W



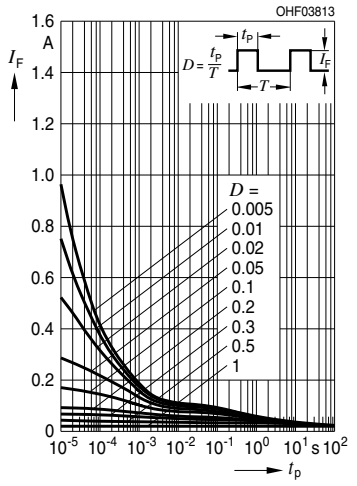
Forward Current
$I_F = f(V_F)$, single pulse, t_p = 100 µs



Permissible Pulse Handling Capability $I_F = f(\tau)$, T_A = 25 °C, duty cycle D = parameter



Permissible Pulse Handling Capability $I_F = f(\tau)$, T_A = 85 °C, duty cycle D = parameter



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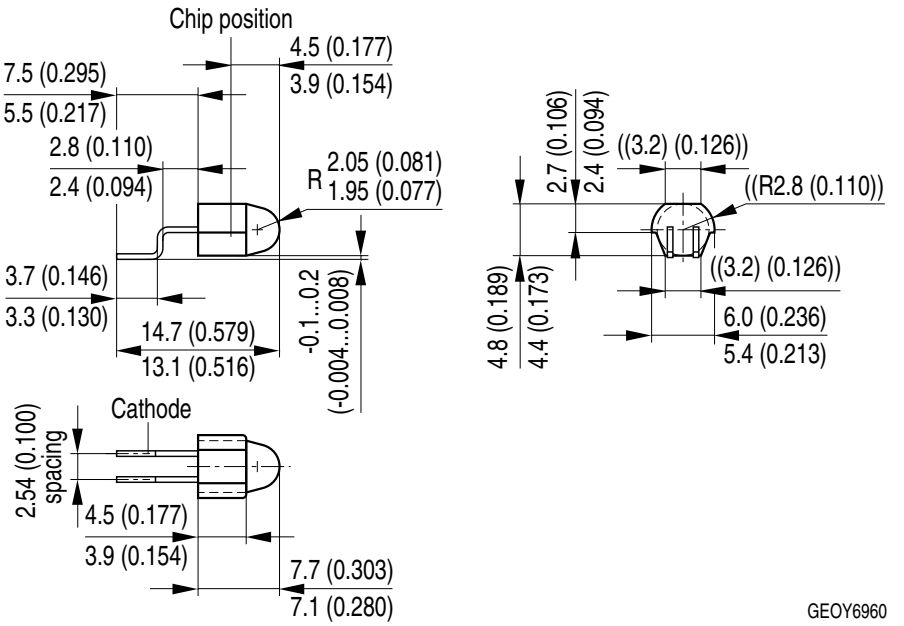
Maßzeichnungen
Package Outlines

SFH 4542



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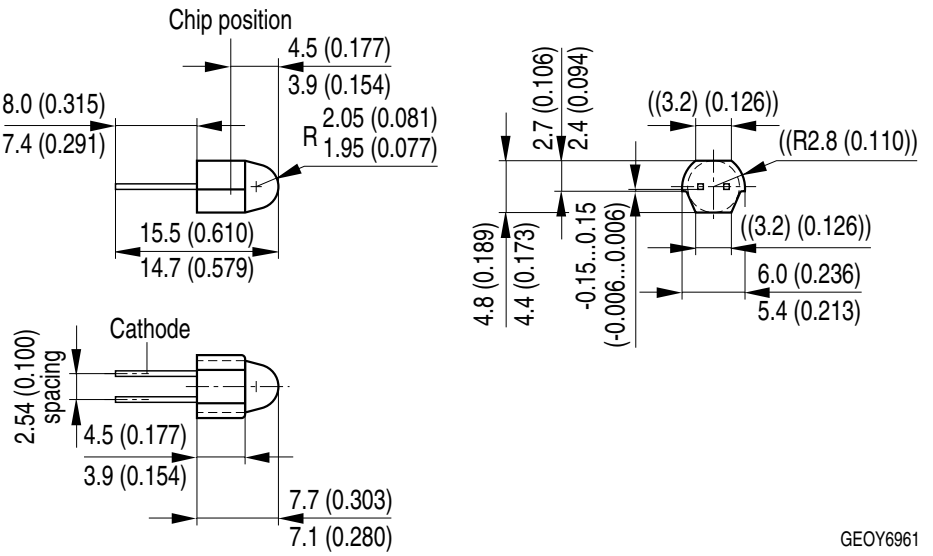
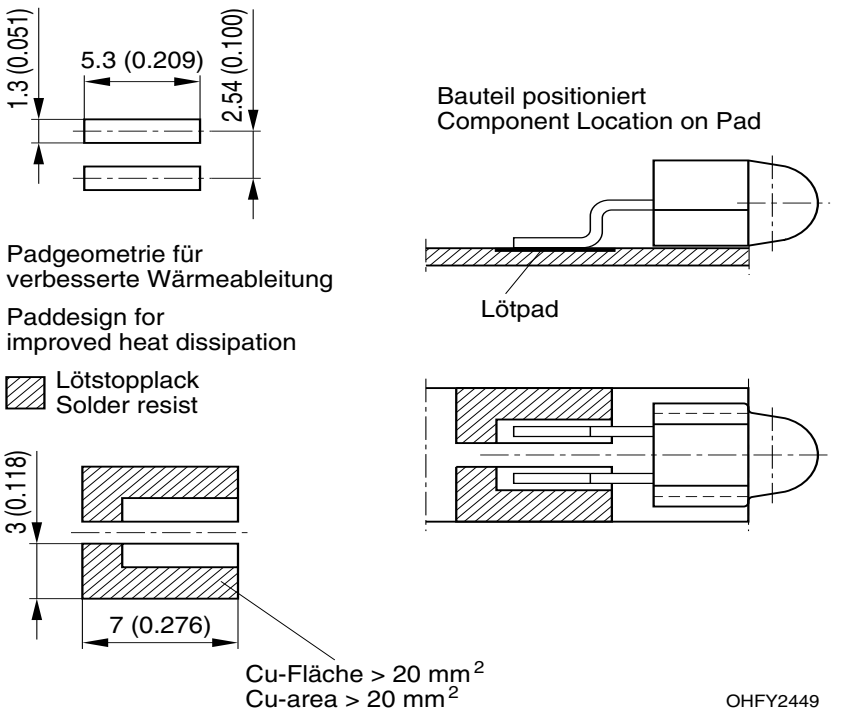


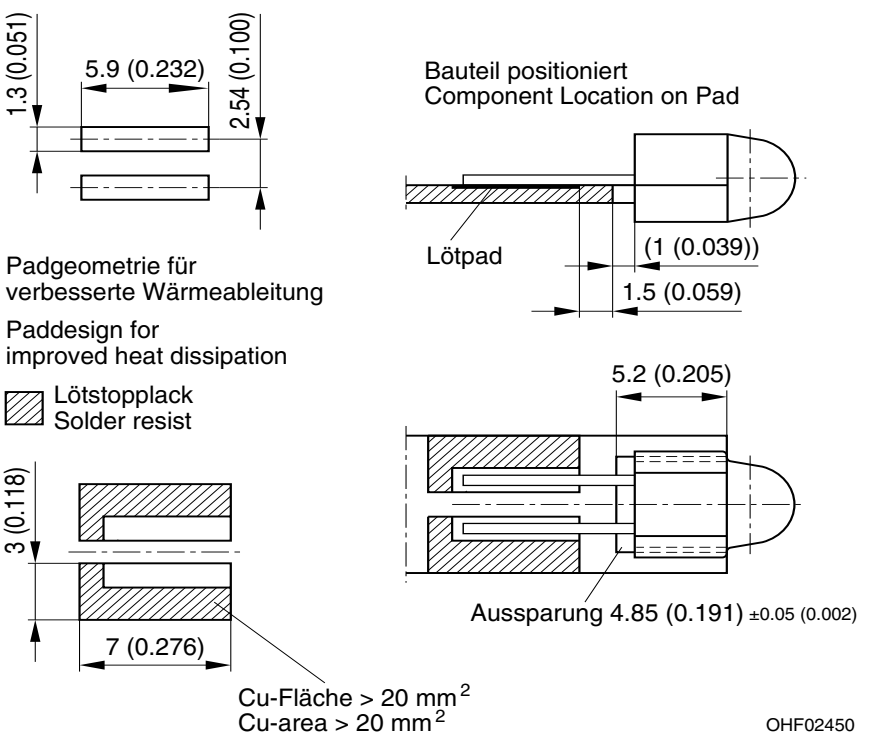
Maße in mm (inch) / Dimensions in mm (inch).

Empfohlenes Lötpaddesign
Recommended Solder Pad

SFH 4542



SFH 4543



Maße in mm (inch) / Dimensions in mm (inch).

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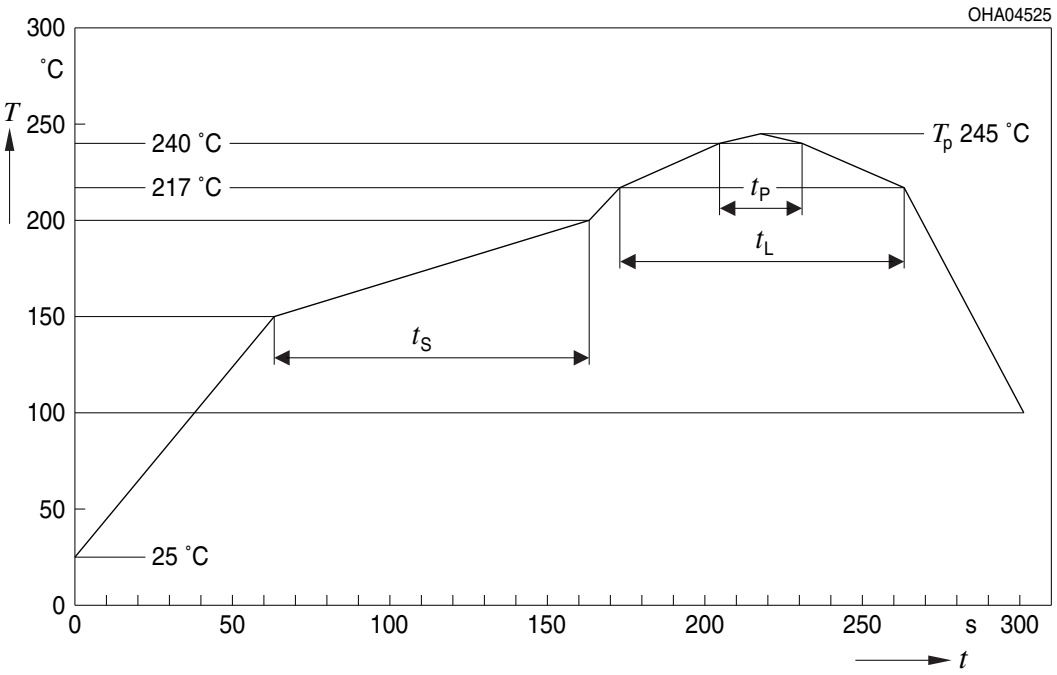
Lötbedingungen
Soldering Conditions
Reflow Lötprofil für bleifreies Löten
Reflow Soldering Profile for lead free soldering

Vorbehandlung nach JEDEC Level 3
Preconditioning acc. to JEDEC Level 3
(nach J-STD-020D.01)
(acc. to J-STD-020D.01)



Profileigenschaften Profile Feature	Bleifreier Aufbau / Pb-Free Assembly (SnAgCu)	
	Empfehlung / Recommendation	Grenzwerte / Max. Ratings
Aufheizrate zum Vorwärmen*) / Ramp-up rate to preheat*) 25 °C to 150 °C	2 K / s	3 K / s
Zeit t_s von T_{Smin} bis T_{Smax} / Time t_s from T_{Smin} to T_{Smax} 150 °C to 200 °C	100 s	min. 60 s max. 120 s
Aufheizrate zur Spitzentemperatur*) / Ramp-up rate to peak*) 180 °C to T_P	2 K / s	3 K / s
Liquidustemperatur T_L / Liquidus temperature T_L	217 °C	
Zeit t_L über T_L / Time t_L above T_L	80 s	max. 100 s
Spitzentemperatur T_P / Peak temperature T_P	245 °C	max. 260 °C
Verweilzeit t_P innerhalb des spezifizierten Spitzentemperaturbereichs T_P - 5 K / Time t_P within the specified peak temperature range T_P - 5 K	20 s	min. 10 s max. 30 s
Abkühlrate*) / Ramp-down rate*) T_P to 100 °C	3 K / s	6 K / s maximum
Zeitspanne von 25 °C bis zur Spitzentemperatur / Time from 25 °C to peak temperature		max. 8 min.

Alle Temperaturen beziehen sich auf die Bauteilmitte, jeweils auf der Bauteiloberseite gemessen / All temperatures refer to the center of the package, measured on the top of the package
* Steigungsberechnung $\Delta T/\Delta t$: Δt max. 5 s; erfüllt über den gesamten Temperaturbereich / slope calculation $\Delta T/\Delta t$: Δt max. 5 s; fulfillment for the whole T-range

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EU RoHS and China RoHS compliant product

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按照中国的相关法规和标准，不含有毒有害物质或元素。

The information describes the type of component and shall not be considered as assured characteristics.
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Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Components used in life-support devices or systems must be expressly authorized for such purpose! Critical components [1] , may only be used in life-support devices or systems [2] with the express written approval of OSRAM OS.

[1] A critical component is a component usedin a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

[2] Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.

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